

Preliminary Specification: Subject to Change without Notice

N-Channel 65 V MOSFET

Product summary

V_{DS} (V)	$R_{DS(on),max}$ (m Ω)	I_D (A)
65	11 @ $V_{GS} = 10V$	61 ⁽¹⁾

Features

- Low $R_{DS(on)}$
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Applications

- DC/DC conversion
- Power switch
- Motor drives

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Package and ordering information

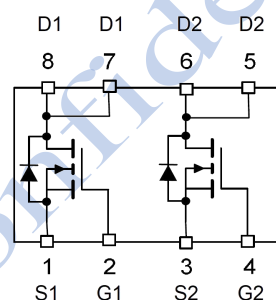
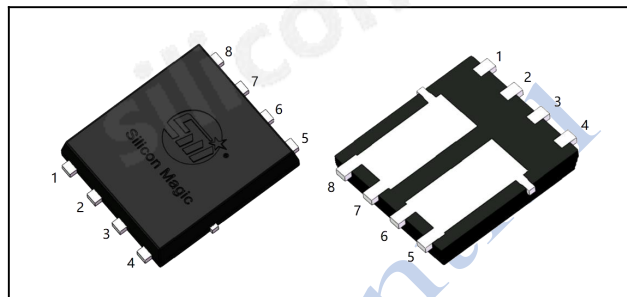
Ordering code	Package	Device code
SDN06K011NN-AA	PDFN5*6-D	N06K011NN-AA

1. Maximum ratings

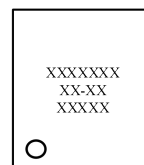
Absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DS}	65	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	61	A
		39	
		16	
Pulsed drain current ⁽²⁾	$I_{D,pulse}$	246	
Avalanche energy, single pulse ⁽³⁾	E_{AS}	130	mJ
Power dissipation	P_D	42	W
		2.7	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

PDFN5*6-D



RoHS
COMPLIANT
HALOGEN
FREE



XXXXXXX
XX-XX
XXXXX
Device code
Lot number
Work week code
Year code

2. Thermal resistance ratings

Thermal resistance ratings				
Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	3.0	°C/W
Thermal resistance, junction-to-ambient ⁽⁴⁾	Steady state	$R_{\theta JA}$	45	

3. Electrical Characteristics

Electrical characteristics (T _J = 25°C unless otherwise noted)						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0, I _D = 250 μA	65			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2	1.9	2.6	V
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		8.7	11	mΩ
		V _{GS} = 4.5 V, I _D = 10 A		14	17.5	
Forward transconductance ⁽⁵⁾	g _{fs}	V _{DS} = 5 V, I _D = 20 A		40		S
Gate resistance	R _g	f = 1MHz		2.5		Ω
Dynamic ⁽⁵⁾						
Total gate charge	Q _g	V _{DS} = 30 V, I _D = 10 A, V _{GS} = 4.5 V		11		nC
Total gate charge	Q _g	V _{DS} = 30 V, I _D = 20 A, V _{GS} = 10 V		19.5		
Gate-source charge	Q _{gs}			3.5		
Gate-drain charge	Q _{gd}			7		
Turn-on delay time	t _{d(on)}	V _{DS} = 30 V, I _D = 20 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		15		ns
Rise time	t _r			40		
Turn-off delay time	t _{d(off)}			38		
Fall time	t _f			15		
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		895		pF
Output capacitance	C _{oss}			300		
Reverse transfer capacitance	C _{rss}			25		
Reverse Diode Characteristics ⁽⁵⁾						
Diode forward voltage	V _{SD}	V _{GS} = 0 V, I _F = 20 A		0.9	1.2	V
Reverse recovery time	t _{rr}	V _{DS} = 30 V, I _F = 20 A, di/dt = 100 A/μs		28		ns
Reverse recovery charge	Q _{rr}			15		nC

Notes

- (1) Limited by maximum junction temperature.
- (2) Pulse width limited by maximum junction temperature.
- (3) $V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, L = 10 \text{ mH}$.
- (4) $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5x1.5 in. board of FR-4 material.
- (5) Guaranteed by design, not subject to production testing.

4. Electrical characteristics diagrams

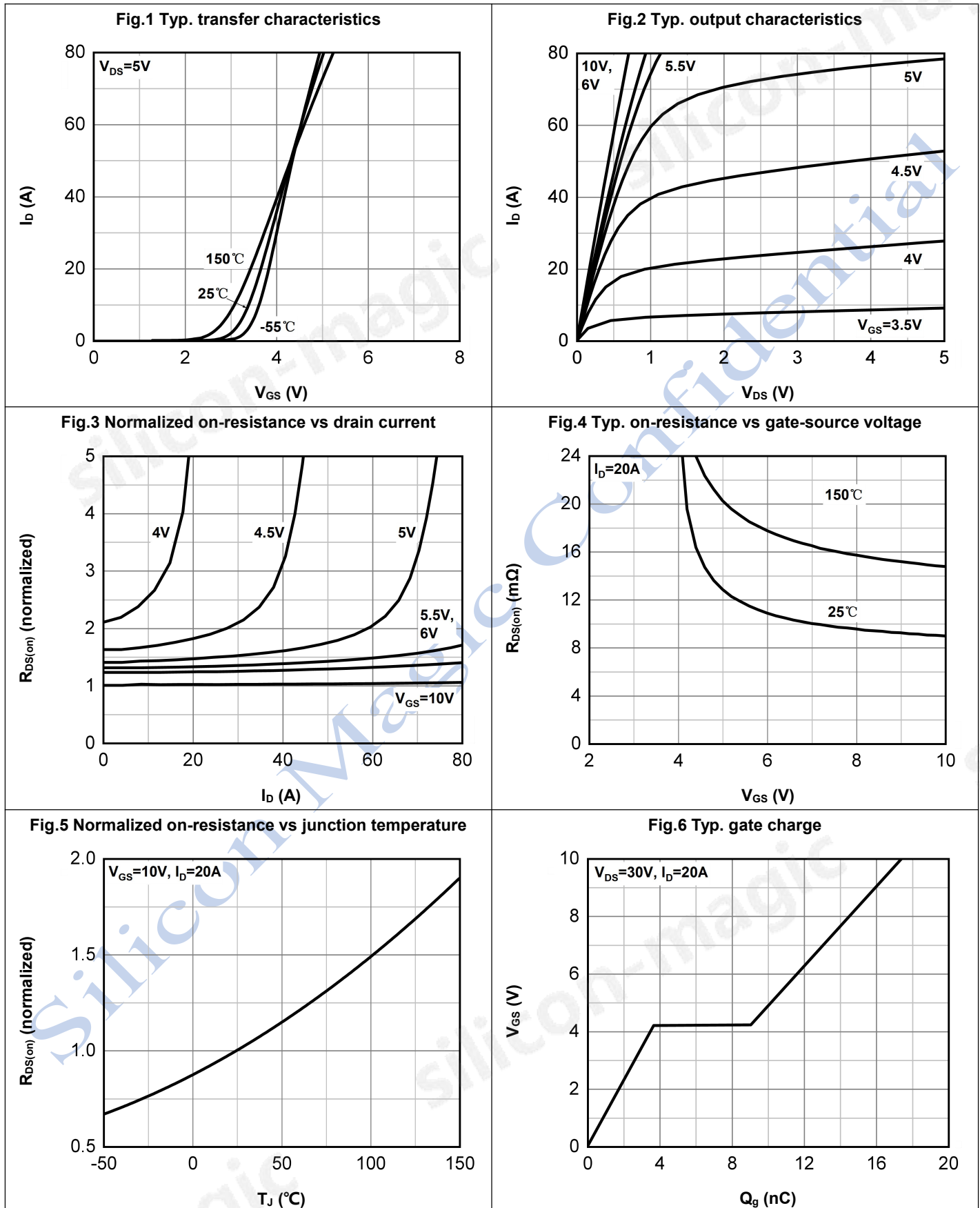


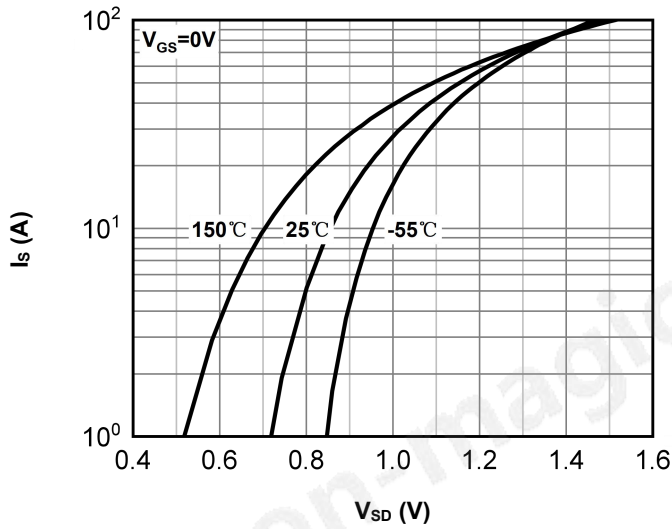
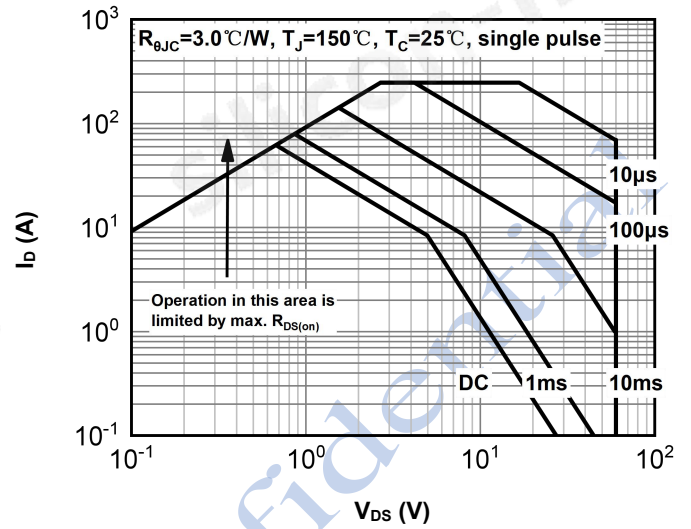
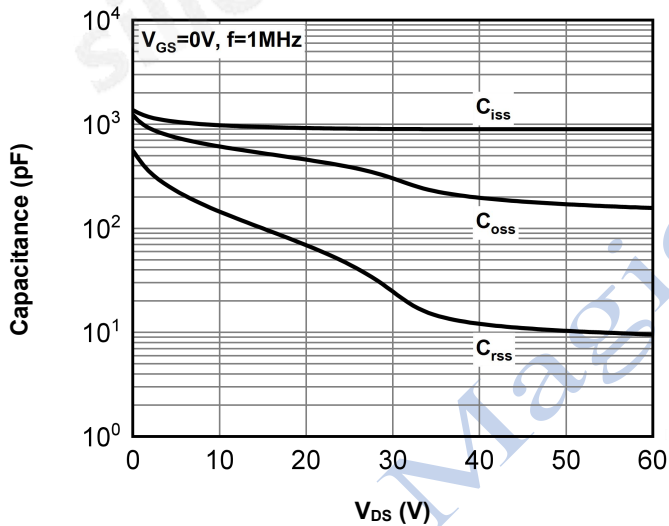
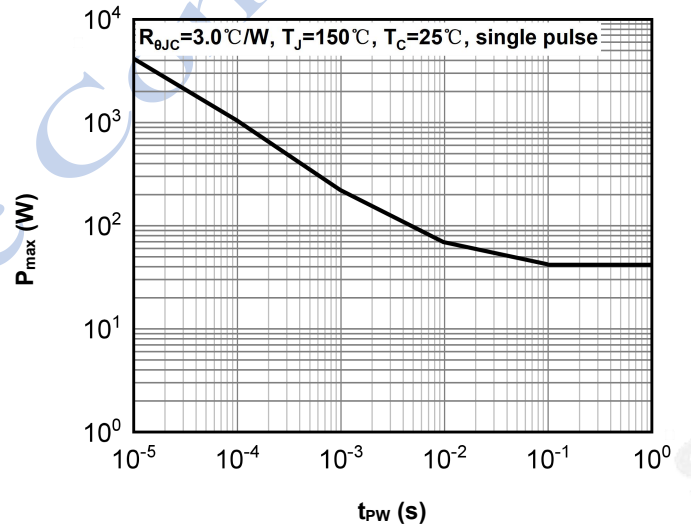
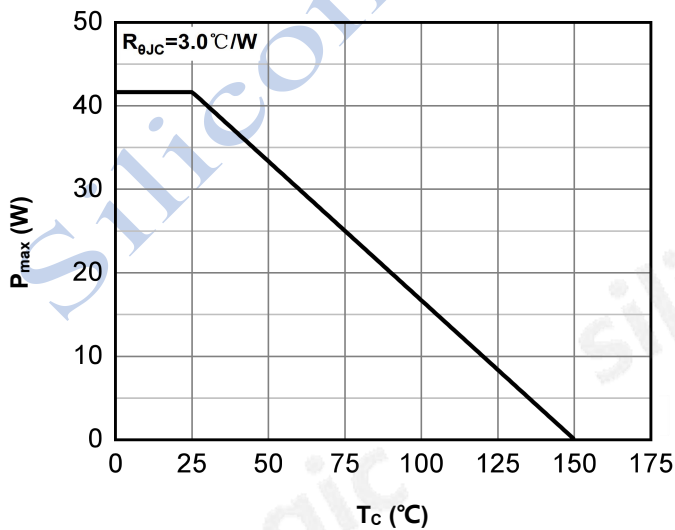
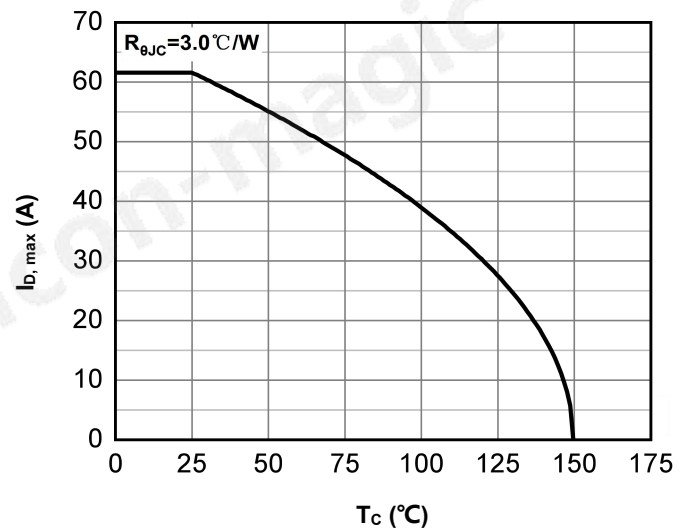
Fig.7 Typ. forward characteristics of body diode

Fig.8 Safe operating area

Fig.9 Typ. Capacitance

Fig.10 Single pulse maximum power dissipation

Fig.11 Max. power dissipation vs case temperature

Fig.12 Max. continuous drain current vs case temperature


Fig.13 Normalized $V_{(BR)DSS}$ vs junction temperature

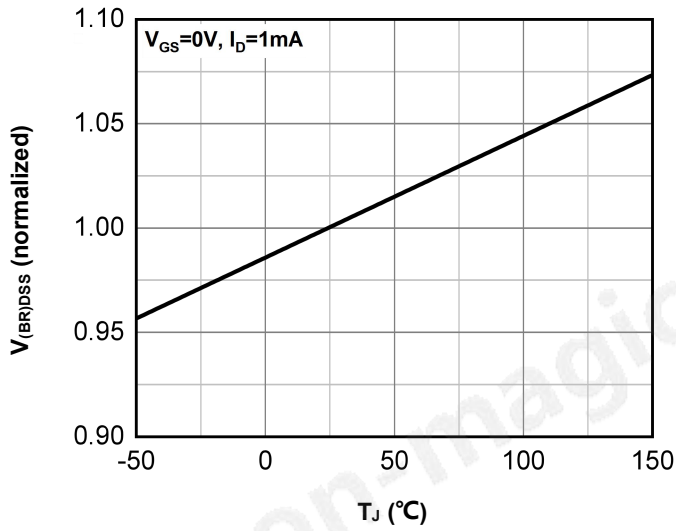


Fig.14 Normalized $V_{GS(th)}$ vs junction temperature

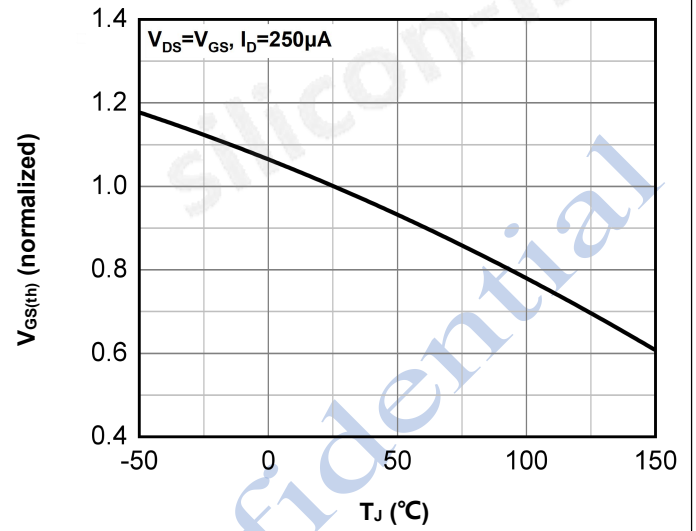
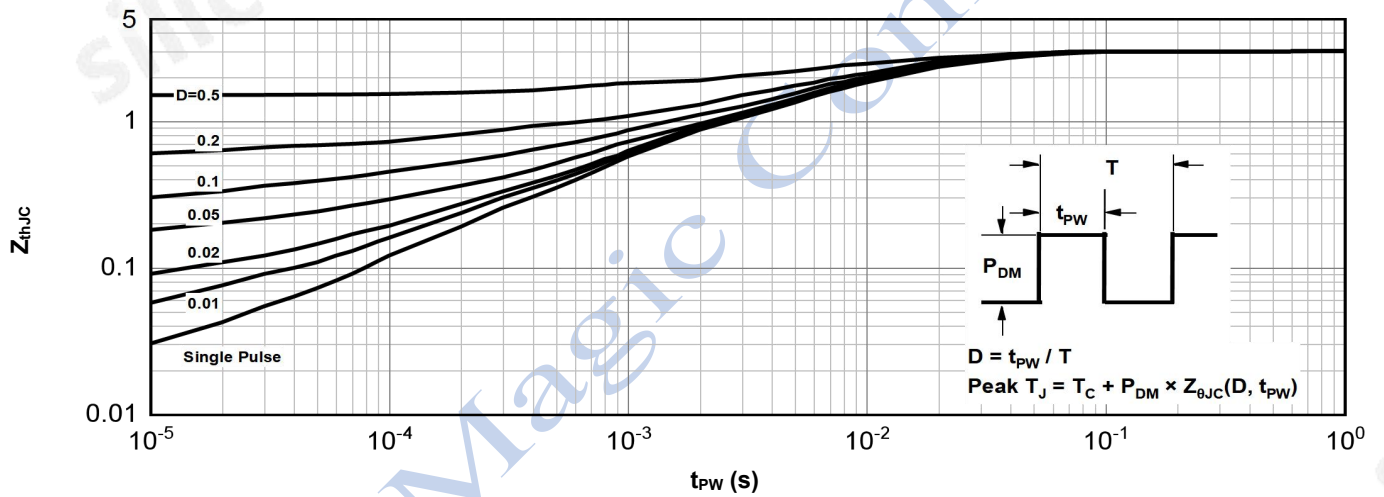
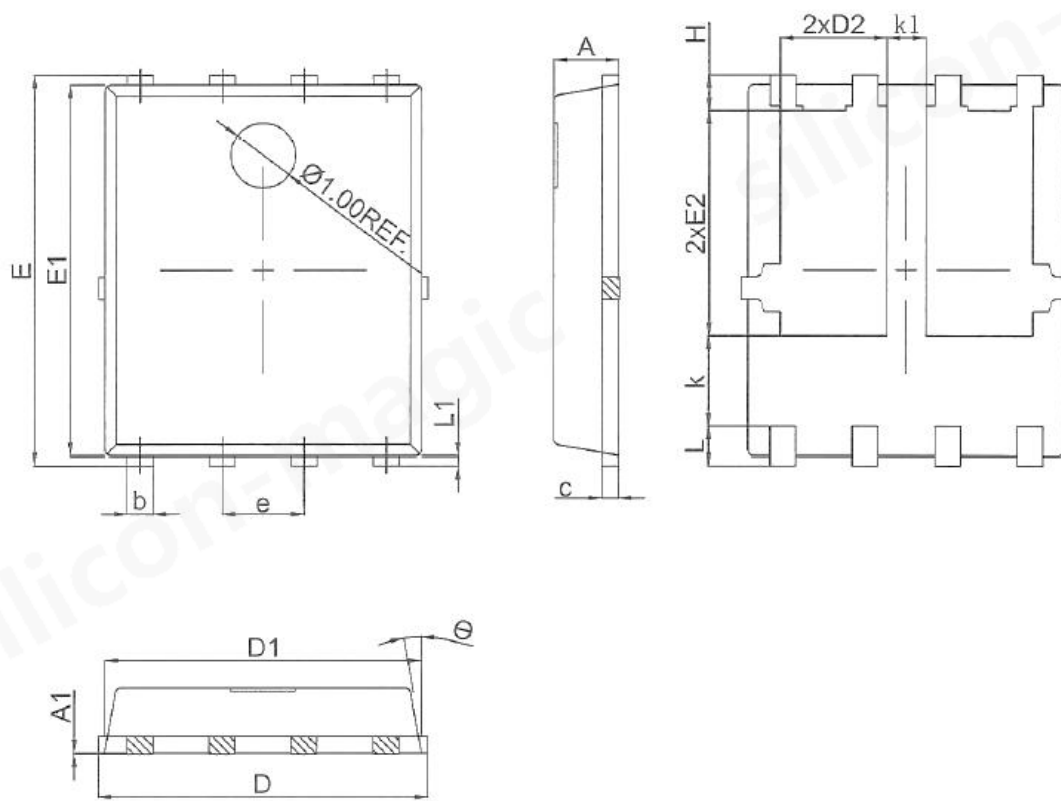


Fig.15 Transient thermal impedance from junction to case



5. Package outline dimensions



Dim	Millimeters		
	Min	Nom	Max
A	0.90	1.00	1.10
A1	—	—	0.05
b	0.30	0.40	0.50
c	0.20	0.25	0.30
D	4.80	5.10	5.40
D1	4.80	4.90	5.00
D2	1.50	1.65	1.80
E	5.95	6.05	6.15
E1	5.65	5.75	5.85
E2	3.34	3.49	3.64
e	1.27 BSC		
H	0.46	0.56	0.66
k	1.10	—	—
k1	0.45	0.60	0.75
L	0.51	0.61	0.71
L1	0.05	0.15	0.25
Θ	8°	10°	12°

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